

CentralTM Semiconductor Corp.

145 Adams Avenue, Hauppauge, NY 11788 USA
Tel: (631) 435-1110 • Fax: (631) 435-1824

Manufacturers of World Class Discrete Semiconductors

CQ48-35B
CQ48-35D
CQ48-35M
CQ48-35N

35 AMP TRIAC
200 THRU 800 VOLTS

JEDEC TO-48 CASE

DESCRIPTION

The CENTRAL SEMICONDUCTOR CQ48-35B series types are Power Triacs, utilizing a Glass Passivated Process, mounted in a hermetically sealed metal case, designed for AC control applications featuring gate triggering in all four (4) quadrants.

MAXIMUM RATINGS $(T_C = 25^\circ\text{C}$ unless otherwise noted)

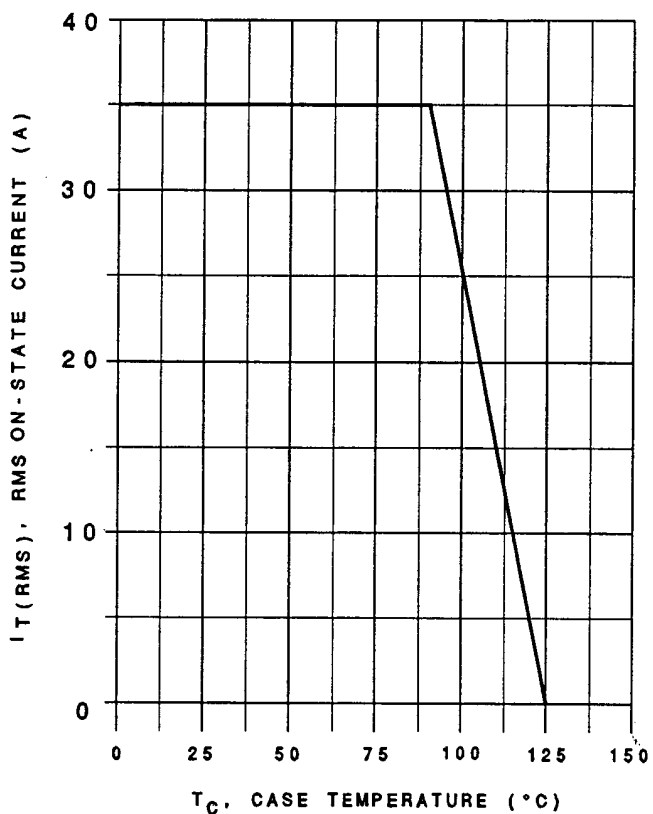
	SYMBOL	CQ48 -35B	CQ48 -35D	CQ48 -35M	CQ48 -35N	UNITS
Peak Repetitive Off-State Voltage	V_{DRM}	200	400	600	800	V
RMS On-State Current $(T_C = 90^\circ\text{C})$	$I_{\text{T(RMS)}}$			35		A
Peak One Cycle Surge $(t = 10\text{ms})$	I_{TSM}			300		A
I^2t Value for Fusing $(t = 10\text{ms})$	I^2t			450		A^2s
Peak Gate Power $(t_p = 10\mu\text{s})$	P_{GM}			40		W
Average Gate Power Dissipation	$P_{\text{G(AV)}}$			1.0		W
Peak Gate Current $(t_p = 10\mu\text{s})$	I_{GM}			6.0		A
Peak Gate Voltage $(t_p = 10\mu\text{s})$	V_{GM}			16		V
Critical Rate of Rise of On-State Current						
Repetitive $(F = 50\text{Hz})$	di/dt			20		$\text{A}/\mu\text{s}$
Storage Temperature	T_{stg}		-40 to +150			$^\circ\text{C}$
Junction Temperature	T_{J}		-40 to +125			$^\circ\text{C}$
Thermal Resistance	$\theta_{\text{J-C}}$			1.1		$^\circ\text{C}/\text{W}$

ELECTRICAL CHARACTERISTICS $(T_C = 25^\circ\text{C}$ unless otherwise noted)

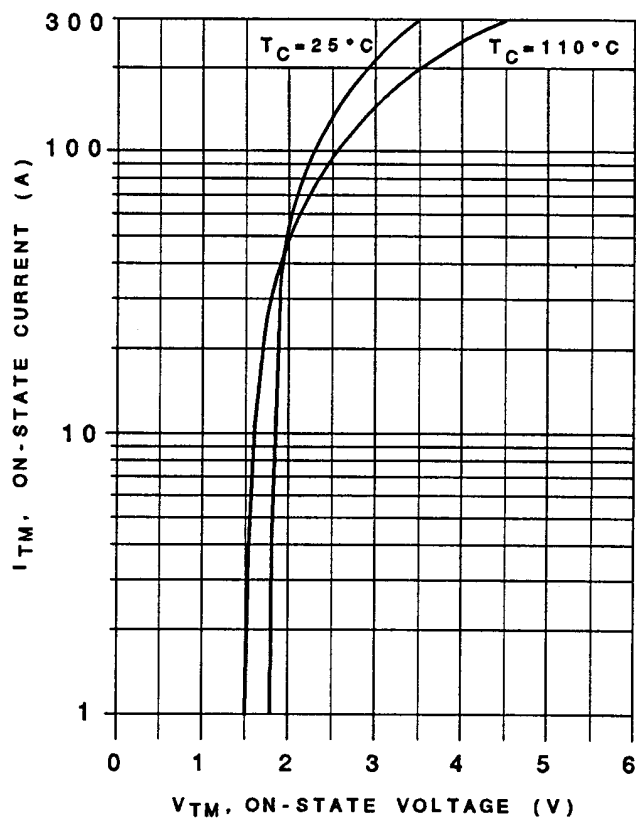
SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I_{DRM}	Rated V_{DRM}			0.02	mA
I_{DRM}	Rated V_{DRM} , $T_C = 110^\circ\text{C}$			4.00	mA
I_{GT}	$V_{\text{D}} = 12\text{V}$, $R_{\text{L}} = 33\Omega$, QUAD I,II,III			100	mA
I_{GT}	$V_{\text{D}} = 12\text{V}$, $R_{\text{L}} = 33\Omega$, QUAD IV			150	mA
I_{H}	$I_{\text{T}} = 500\text{mA}$			100	mA
V_{GT}	$V_{\text{D}} = 12\text{V}$, $R_{\text{L}} = 33\Omega$, QUAD I,II,III,IV			1.50	V
V_{TM}	$I_{\text{TM}} = 49\text{A}$, $t_p = 10\text{ms}$			2.00	V
dv/dt	$V_{\text{D}} = \frac{2}{3}V_{\text{DRM}}$, $R_{\text{GK}} = \infty$, $T_C = 110^\circ\text{C}$	250			$\text{V}/\mu\text{s}$

CQ48-35B SERIES RATING AND CHARACTERISTIC CURVES

RMS ON-STATE CURRENT vs. CASE TEMPERATURE



MAXIMUM ON-STATE CHARACTERISTICS



MECHANICAL DIMENSIONS

